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1 pC Charge Injection, 100 pA Leakage CMOS ± 5 V/5 V/3 V 4-Channel Multiplexer

ADG604

FEATURES

1 pC Charge Injection (Over the Full Signal Range) ± 2.7 V to ± 5.5 V Dual Supply 2.7 V to 5.5 V Single Supply Automotive Temperature Range: -40° C to $+125^{\circ}$ C 100 pA Max @ 25°C Leakage Currents 85 Ω Typ On Resistance Rail-to-Rail Operation Fast Switching Times Typical Power Consumption (<0.1 μ W) TTL/CMOS Compatible Inputs 14-Lead TSSOP Package

APPLICATIONS

Automatic Test Equipment
Data Acquisition Systems
Battery-Powered Instruments
Communication Systems
Sample and Hold Systems
Remote-Powered Equipment
Audio and Video Signal Routing
Relay Replacement
Avionics

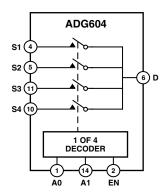
GENERAL DESCRIPTION

The ADG604 is a CMOS analog multiplexer, comprising four single channels. It operates from a dual supply of ± 2.7 V to ± 5.5 V, or from a single supply of 2.7 V to 5.5 V.

The ADG604 switches one of four inputs to a common output, D, as determined by the 3-bit binary address lines, A0, A1, and EN. A Logic "0" on the EN pin disables the device.

The ADG604 offers ultralow charge injection of ± 1.5 pC over the entire signal range and leakage currents of 10 pA typical at 25°C. It offers on resistance of 85 Ω typ, which is matched to within 2 Ω between channels. The ADG604 also has low power dissipation yet gives high switching speeds. The ADG604 is available in a 14-lead TSSOP package.

FUNCTIONAL BLOCK DIAGRAM



PRODUCT HIGHLIGHTS

- 1. Ultralow Charge Injection (Q $_{INJ}$: ± 1.5 pC Typ over the Full Signal Range)
- 2. Leakage Current <0.5 nA max @ 85°C
- 3. Dual ± 2.7 V to ± 5.5 V or Single 2.7 V to 5.5 V Supply
- 4. Fully Specified to 125°C
- 5. Small 14-Lead TSSOP Package

ADG604* PRODUCT PAGE QUICK LINKS

Last Content Update: 02/23/2017

COMPARABLE PARTS 🖳

View a parametric search of comparable parts.

DOCUMENTATION

Application Notes

• AN-1024: How to Calculate the Settling Time and Sampling Rate of a Multiplexer

Data Sheet

 ADG604: 1 pC Charge Injection, 100 pA Leakage CMOS ±5 V/5 V/3 V 4-Channel Multiplexer Data Sheet

REFERENCE MATERIALS •

Product Selection Guide

• Switches and Multiplexers Product Selection Guide

Technical Articles

- · CMOS Switches Offer High Performance in Low Power, **Wideband Applications**
- Data-acquisition system uses fault protection
- Enhanced Multiplexing for MEMS Optical Cross Connects
- · Temperature monitor measures three thermal zones

DESIGN RESOURCES 🖵

- · ADG604 Material Declaration
- PCN-PDN Information
- · Quality And Reliability
- Symbols and Footprints

DISCUSSIONS 🖳



View all ADG604 EngineerZone Discussions.

SAMPLE AND BUY 🖳

Visit the product page to see pricing options.

TECHNICAL SUPPORT

Submit a technical question or find your regional support number.

DOCUMENT FEEDBACK \Box

Submit feedback for this data sheet.

ADG604-SPECIFICATIONS

Parameter	25°C	-40°C to +85°C	-40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			V_{SS} to V_{DD}	V	
					$V_{DD} = +4.5 \text{ V}, V_{SS} = -4.5 \text{ V}$
On Resistance (R _{ON})	85	140	160	ΩTyp	$V_S = \pm 3 \text{ V}, I_S = -1 \text{ mA},$
On Resistance Match Between	115	140	160	Ω Max	Test Circuit 1
Channels (ΔR_{ON})	2			ΩТур	$V_S = \pm 3 \text{ V}, I_S = -1 \text{ mA}$
	4	5.5	6.5	Ω Max	.3
On-Resistance Flatness (R _{FLAT(ON)})	25			ΩТур	$V_{S} = \pm 3 \text{ V}, I_{S} = -1 \text{ mA}$
	40	55	60	Ω Max	
LEAKAGE CURRENTS					$V_{\rm DD}$ = +5.5 V, $V_{\rm SS}$ = -5.5 V
Source OFF Leakage I _S (OFF)	±0.01			nA Typ	$V_{S} = \pm 4.5 \text{ V}, V_{D} = \mp 4.5 \text{ V},$
D : OFFI I I (OFFI)	±0.1	± 0.25	± 4	nA Max	Test Circuit 2
Drain OFF Leakage I _D (OFF)	±0.01	105	1.0	nA Typ	$V_S = \pm 4.5 \text{ V}, V_D = \mp 4.5 \text{ V},$
Channel ON Leakage I _D , I _S (ON)	±0.1 ±0.01	±0.5	±8	nA Max nA Typ	Test Circuit 2 $V_S = V_D = \pm 4.5 \text{ V}$, Test Circuit 3
Chainer Oly Deakage ID, 18 (Oly)	± 0.01	±0.5	±10	nA Max	vs – vb – ±4.5 v, Test Gheuit 5
DIGITAL INPUTS					
Input High Voltage, V_{INH}			2.4	V Min	
Input Low Voltage, V _{INL}			0.8	V Max	
Input Current					
${ m I}_{ m INL}$ or ${ m I}_{ m INH}$	0.005			μА Тур	$V_{IN} = V_{INL}$ or V_{INH}
			± 0.1	μA Max	
C _{IN} , Digital Input Capacitance	2			pF Typ	
DYNAMIC CHARACTERISTICS ²					
Transition Time	70	100	150	ns Typ	$V_{S1} = +3 \text{ V}, V_{S4} = -3 \text{ V}, R_L = 300 \Omega,$
+ Enghlo	100 80	120	150	ns Max ns Typ	$C_L = 35 \text{ pF}, \text{ Test Circuit 4}$ $R_L = 300 \Omega, C_L = 35 \text{ pF}$
t _{ON} Enable	105	130	150	ns Max	$V_S = 3 \text{ V}$, Test Circuit 6
t _{OFF} Enable	30	130	150	ns Typ	$R_L = 300 \Omega$, $C_L = 35 pF$
	45	55	65	ns Max	$V_S = 3 \text{ V}$, Test Circuit 6
Break-Before-Make Time Delay, t_{BBM}	20			ns Typ	$R_L = 300 \Omega, C_L = 35 pF,$
			10	ns Min	$V_{S1} = V_{S2} = 3 \text{ V, Test Circuit 5}$
Charge Injection Off Isolation	-1 75			pC Typ	$V_S = 0 \text{ V}, R_S = 0 \Omega, C_L = 1 \text{nF}, \text{ Test Circuit 7}$
Off Isolation	-75			dB Typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 10 MHz$, Test Circuit 8
Channel-to-Channel Crosstalk	-70			dB Typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 10 MHz$, Test Circuit 10
Bandwidth –3 dB	280			MHz Typ	$R_L = 50 \Omega$, $C_L = 5 pF$, Test Circuit 9
C_{S} (OFF)	5			pF Typ	f = 1 MHz
C_D (OFF)	17			pF Typ	f = 1 MHz
$C_D, C_S(ON)$	18			pF Typ	f = 1 MHz
POWER REQUIREMENTS					$V_{\rm DD}$ = +5.5 V, $V_{\rm SS}$ = -5.5 V
I_{DD}	0.001			μА Тур	Digital Inputs = 0 V or 5.5 V
Tan	0.001		1.0	μA Max	Digital Inguita = 0 V = 7.5.5 V
Iss	0.001		1.0	μΑ Тур μΑ Мах	Digital Inputs = 0 V or 5.5 V
	1		1.0	MI IVIAN	

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NOTES

1Y Version Temperature Range: -40°C to +125°C

²Guaranteed by design, not subject to production test.

Specifications subject to change without notice.

 $\textbf{SINGLE SUPPLY}^{1} \ \, (\textit{V}_{DD} = 5 \ \textit{V} \ \pm \ 10\%, \textit{V}_{SS} = 0 \ \textit{V}, \ \textit{GND} = 0 \ \textit{V}. \ \textit{All specifications} \ -40^{\circ}\textrm{C} \ to \ +125^{\circ}\textrm{C} \ unless \ otherwise \ noted.)$

Parameter	25°C	-40°C to +85°C	-40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			$0~\mathrm{V}$ to V_{DD}	V	
					$V_{DD} = 4.5 \text{ V}, V_{SS} = 0 \text{ V}$
On Resistance (R _{ON})	210			ΩTyp	$V_S = 3.5 \text{ V}, I_S = -1 \text{ mA},$
	290	350	380	Ω Max	Test Circuit 1
On Resistance Match Between					
Channels (ΔR_{ON})	3			ΩТур	$V_S = 3.5 \text{ V}, I_S = -1 \text{ mA}$
		12	13	Ω Max	
LEAKAGE CURRENTS					$V_{\mathrm{DD}} = 5.5 \mathrm{V}$
Source OFF Leakage I _S (OFF)	±0.01			nA Typ	$V_S = 1 \text{ V}/4.5 \text{ V}, V_D = 4.5 \text{ V}/1 \text{ V},$
	±0.1	± 0.25	± 4	nA Max	Test Circuit 2
Drain OFF Leakage I _D (OFF)	±0.01			nA Typ	$V_S = 1 \text{ V}/4.5 \text{ V}, V_D = 4.5 \text{ V}/1 \text{ V},$
	±0.1	± 0.5	±8	nA Max	Test Circuit 2
Channel ON Leakage I_D , I_S (ON)	±0.01		10	nA Typ	$V_S = V_D = 4.5 \text{ V/1 V},$
	±0.1	±0.5	10	nA Max	Test Circuit 3
DIGITAL INPUTS					
Input High Voltage, V _{INH}			2.4	V Min	
Input Low Voltage, V _{INL}			0.8	V Max	
Input Current					
I_{INL} or I_{INH}	0.005			μА Тур	$V_{IN} = V_{INL}$ or V_{INH}
0 D:: 11 . 0 .:			± 0.1	μA Max	
C _{IN} , Digital Input Capacitance	2			pF Typ	
DYNAMIC CHARACTERISTICS ²					
Transition Time	90			ns Typ	$V_{S1} = 3 \text{ V}, V_{S4} = 0 \text{ V}, R_L = 300 \Omega,$
	150	185	210	ns Max	$C_L = 35 \text{ pF}$, Test Circuit 4
t _{ON} Enable	105	100	222	ns Typ	$R_L = 300 \Omega, C_L = 35 pF$
. F 11	150	190	220	ns Max	$V_S = 3 \text{ V}$, Test Circuit 6
t _{OFF} Enable	45 70	80	90	ns Typ ns Max	$R_L = 300 \Omega$, $C_L = 35 pF$ $V_S = 3 V$, Test Circuit 6
Break-Before-Make Time Delay, t _{BBM}	30	80	90	ns Typ	$R_L = 300 \Omega$, $C_L = 35 pF$,
break-before-make Time Delay, t _{BBM}	30		10	ns Typ	$V_{S1} = V_{S2} = 3 \text{ V}, \text{ Test Circuit 5}$
Charge Injection	0.3		10	pC Typ	$V_S = 0 \text{ V}, R_S = 0 \Omega, C_L = 1 \text{ nF},$
Charge injection	0.5			porp	Test Circuit 7
Off Isolation	-65			dB Typ	$R_{L} = 50 \Omega$, $C_{L} = 5 pF$, $f = 10 MHz$,
				J.I	Test Circuit 8
Channel-to-Channel Crosstalk	-70			dB Typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 10 MHz$,
					Test Circuit 10
Bandwidth -3 dB	250			MHz Typ	$R_L = 50 \Omega$, $C_L = 5 pF$, Test Circuit 9
C_{S} (OFF)	5			pF Typ	f = 1 MHz
$C_{\rm D}$ (OFF)	17			pF Typ	f = 1 MHz
$C_D, C_S(ON)$	18			pF Typ	f = 1 MHz
POWER REQUIREMENTS					$V_{\mathrm{DD}} = 5.5 \mathrm{V}$
					Digital Inputs = 0 V or 5.5 V
$I_{ m DD}$	0.001			μА Тур	
			1.0	μΑ Max	

Specifications subject to change without notice.

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¹Y Version Temperature Range: -40°C to +125°C ²Guaranteed by design, not subject to production test.

ADG604-SPECIFICATIONS

SINGLE SUPPLY¹ $(V_{DD}=3~V~\pm~10\%,~V_{SS}=0~V,~GND=0~V.~All~specifications~-40°C~to~+125°C~unless~otherwise~noted.)$

Parameter	25°C	-40°C to +85°C	-40°C to +125°C	Unit	Test Conditions/Comments
ANALOG SWITCH					
Analog Signal Range			0 V to V_{DD}	V	
On Resistance (R _{ON})	380	420	460	Ω Τур	$V_{\rm DD} = 2.7 \text{ V}, V_{\rm SS} = 0 \text{ V}$ $V_{\rm S} = 1.5 \text{ V}, I_{\rm S} = -1 \text{ mA},$ Test Circuit 1
On Resistance Match Between Channels (ΔR_{ON})			5	ΩТур	$V_S = 1.5 \text{ V}, I_S = -1 \text{ mA}$
LEAKAGE CURRENTS					$V_{DD} = 3.3 \text{ V}$
Source OFF Leakage I _S (OFF)	± 0.01			nA Typ	$V_S = 1 \text{ V/3 V}, V_D = 3 \text{ V/1 V},$
	± 0.1	± 0.25	± 4	nA Max	Test Circuit 2
Drain OFF Leakage I _D (OFF)	± 0.01			nA Typ	$V_S = 1 \text{ V/3 V}, V_D = 3 \text{ V/1 V},$
	± 0.1	± 0.5	±8	nA Max	Test Circuit 2
Channel ON Leakage I _D , I _S (ON)	± 0.01			nA Typ	$V_S = V_D = 1 \text{ V/3 V},$
	±0.1	±0.5	±10	nA Max	Test Circuit 3
DIGITAL INPUTS					
Input High Voltage, V _{INH}			2.0	V Min	
Input Low Voltage, V _{INL}			0.8	V Max	
Input Current					
I _{INL} or I _{INH}	0.005			μА Тур	$V_{IN} = V_{INL}$ or V_{INH}
			± 0.1	μA Max	
C _{IN} , Digital Input Capacitance	2			pF Typ	
DYNAMIC CHARACTERISTICS ²					
Transition Time	170			ns Typ	$V_{S1} = 2 \text{ V}, V_{S4} = 0 \text{ V}, R_{L} = 300 \Omega,$
	320	390	450	ns Max	$C_L = 35 \text{ pF}$, Test Circuit 4
t _{ON} Enable	180			ns Typ	$R_{L} = 300 \Omega, C_{L} = 35 pF$
	250	265	390	ns Max	$V_S = 2 V$, Test Circuit 6
t _{OFF} Enable	100			ns Typ	$R_L = 300 \Omega, C_L = 35 pF$
	160	205	225	ns Max	$V_S = 2 \text{ V}$, Test Circuit 6
Break-Before-Make Time Delay, $t_{\rm BBM}$	100		10	ns Typ	$R_L = 300 \Omega, C_L = 35 pF,$
Change Indication	0.2		10	ns Min	$V_{S1} = V_{S2} = 2 \text{ V}$, Test Circuit 5
Charge Injection	0.3			pC Typ	$V_S = 0$ V to 3.3 V, $R_S = 0$ Ω , $C_L = 1$ μ F, Test Circuit 7
Off Isolation	-65			dB Typ	R _L = 50 Ω , C _L = 5 pF, f = 10 MHz, Test Circuit 8
Channel-to-Channel Crosstalk	70			dB Typ	$R_L = 50 \Omega$, $C_L = 5 pF$, $f = 10 MHz$, Test Circuit 10
Bandwidth -3 dB	250			MHz Typ	$R_L = 50 \Omega$, $C_L = 5 pF$, Test Circuit 9
C_{S} (OFF)	5			pF Typ	f = 1 MHz
$C_{\rm D}$ (OFF)	17			pF Typ	f = 1 MHz
$C_D, C_S(ON)$	18			pF Typ	f = 1 MHz
POWER REQUIREMENTS					V _{DD} = 3.3 V Digital Inputs = 0 V or 3.3 V
I_{DD}	0.001			μА Тур	g
עע			1.0	μΑ Max	
				F	

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NOTES 1 Y Version Temperature Range: -40° C to $+125^{\circ}$ C

²Guaranteed by design, not subject to production test.

Specifications subject to change without notice.

ABSOLUTE MAXIMUM RATINGS¹

$(T_A = 25^{\circ}C \text{ unless otherwise noted})$
V_{DD} to V_{SS}
V_{DD} to GND $$ $$ –0.3 V to +6.5 V $$
V_{SS} to GND $\dots \dots \dots \dots \dots \dots + 0.3~V$ to –6.5 V
Analog Inputs ² V_{SS} –0.3 V to V_{DD} + 0.3 V
Digital Inputs ² -0.3 V to $V_{DD} + 0.3 \text{ V}$ or
30 mA, Whichever Occurs First
Peak Current, S or D
(Pulsed at 1 ms, 10% Duty Cycle Max)
Continuous Current, S or D 10 mA
Operating Temperature Range
Automotive (Y Version)
Storage Temperature Range $\ \dots \dots -65^{\circ}C$ to +150°C

Junction Temperature	150°C
TSSOP Package	
θ_{IA} Thermal Impedance	0°C/W
θ_{IC} Thermal Impedance	7°C/W
Lead Temperature, Soldering (10 seconds)	300°C
IR Reflow, Peak Temperature	220°C

¹Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those listed in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Only one absolute maximum rating may be applied at any one time.

²Overvoltages at EN, A0, A1, S, or D will be clamped by internal diodes. Current should be limited to the maximum ratings given.

ORDERING GUIDE

Model Option	Temperature Range	Package Description	Package
ADG604YRU	−40°C to +125°C	Thin Shrink Small Outline (TSSOP)	RU-14

PIN CONFIGURATION

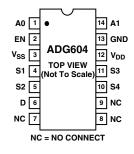


Table I. Truth Table

A1	A0	EN	ON Switch
X	X	0	None
0	0	1	1
0	1	1	2
1	0	1	3
1	1	1	4

CAUTION_

ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although the ADG604 features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high-energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.



REV. 0 -5-

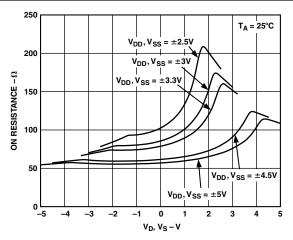
ADG604

TERMINOLOGY

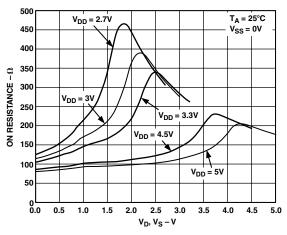
	TERMINOLOGY
$\overline{V_{\mathrm{DD}}}$	Most Positive Power Supply Potential
V_{SS}	Most Negative Power Supply in a Dual Supply Application. In single supply applications, this should be tied to
	ground at the device.
GND	Ground (0 V) Reference
$I_{ m DD}$	Positive Supply Current
I_{SS}	Negative Supply Current
S	Source Terminal. May be an input or output.
D	Drain Terminal. May be an input or output.
R_{ON}	Ohmic Resistance between D and S
$\Delta R_{ m ON}$	On Resistance Match between any two channels, i.e., R_{ON} Max – R_{ON} Min
$R_{FLAT(ON)}$	Flatness is defined as the difference between the maximum and minimum value of On resistance as measured
	over the specified analog signal range.
I _S (OFF)	Source Leakage Current with the Switch "OFF"
I_D (OFF)	Drain Leakage Current with the Switch "OFF"
$I_D, I_S (ON)$	Channel Leakage Current with the Switch "ON"
V_D, V_S	Analog Voltage on Terminals D, S
V_{INL}	Maximum Input Voltage for Logic "0"
V_{INH}	Minimum Input Voltage for Logic "1"
I_{INL} (I_{INH})	Input Current of the Digital Input
C _s (OFF)	Channel Input Capacitance for "OFF" Condition
C_D (OFF)	Channel Output Capacitance for "OFF" Condition
$C_D, C_S (ON)$	"On" Switch Capacitance
C_{IN}	Digital Input Capacitance
t_{ON} (EN)	Delay time between the 50% and 90% points of the digital input and switch "ON" condition.
t _{OFF} (EN)	Delay time between the 50% and 90% points of the digital input and switch "OFF" condition.
t _{TRANSITION}	Delay time between the 50% and 90% points of the digital input and switch "ON" condition when switching
	from one address state to another.
$t_{ m BBM}$	"OFF" time or "ON" time measured between the 80% points of both switches, when switching from one address
Character Indianation	state to another.
Charge Injection	A measure of the glitch impulse transferred from the digital input to the analog output during switching.
Crosstalk	A measure of unwanted signal that is coupled through from one channel to another as a result of parasitic capacitance.
Off Isolation Bandwidth	A measure of unwanted signal coupling through an "On" switch.
Insertion Loss	Frequency Response of the "On" Switch Loss Due to the On Resistance of the Switch
msertion Loss	Loss Due to the On Resistance of the Switch

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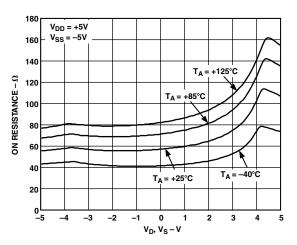
Typical Performance Characteristics—ADG604



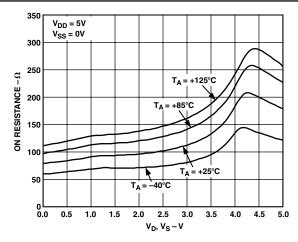
TPC 1. On Resistance vs. V_D (V_S), Dual Supply



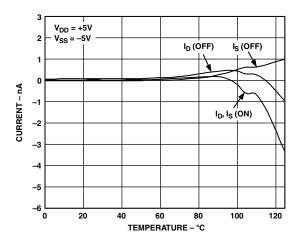
TPC 2. On Resistance vs. V_D (V_S), Single Supply



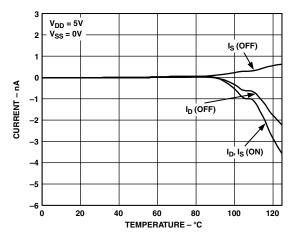
TPC 3. On Resistance vs. V_D (V_S) for Different Temperatures, Dual Supply



TPC 4. On Resistance vs. V_D (V_S) for Different Temperatures, Single Supply



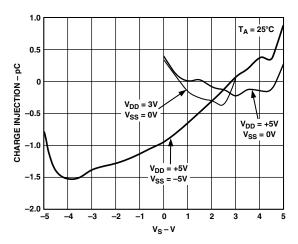
TPC 5. Leakage Currents vs. Temperature, Dual Supply



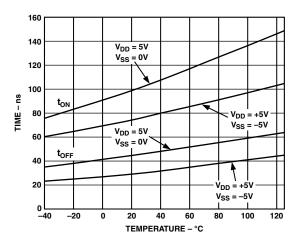
TPC 6. Leakage Currents vs. Temperature, Single Supply

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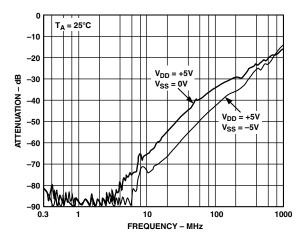
ADG604



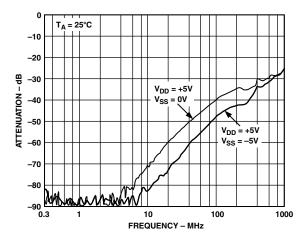
TPC 7. Charge Injection vs. Source Voltage



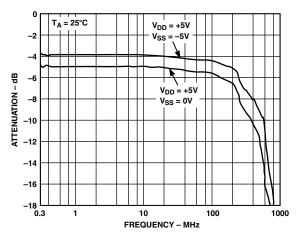
TPC 8. t_{ON}/t_{OFF} Times vs. Temperature



TPC 9. Off Isolation vs. Frequency



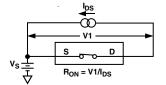
TPC 10. Crosstalk vs. Frequency



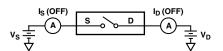
TPC 11. On Response vs. Frequency

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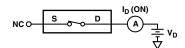
Test Circuits



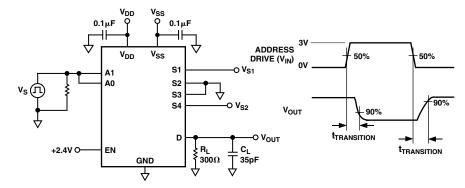
Test Circuit 1. On Resistance



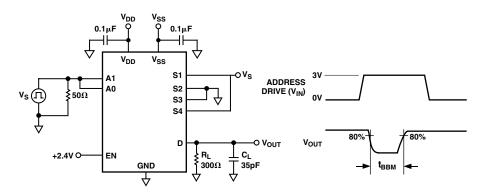
Test Circuit 2. Off Leakage



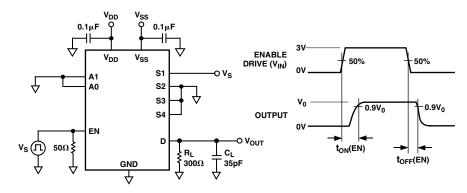
Test Circuit 3. On Leakage



Test Circuit 4. Switching Time of Multiplexer, t_{TRANSITION}



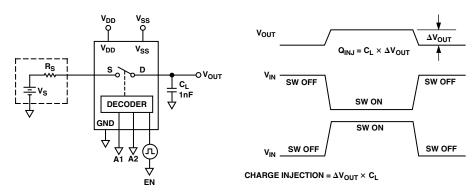
Test Circuit 5. Break-Before-Make Delay, t_{BBM}



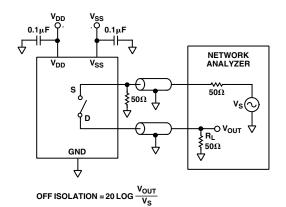
Test Circuit 6. Enable Delay, t_{ON} (EN), t_{OFF} (EN)

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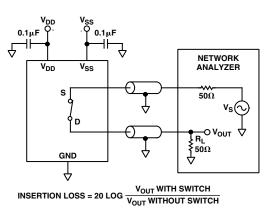
ADG604



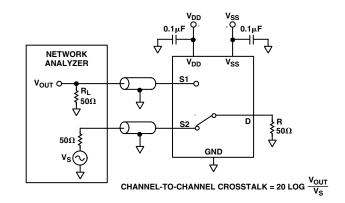
Test Circuit 7. Charge Injection



Test Circuit 8. Off Isolation



Test Circuit 9. Bandwidth

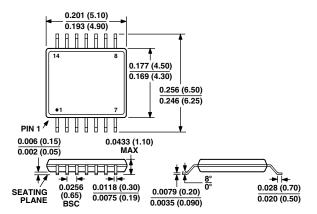


Test Circuit 10. Channel-to-Channel Crosstalk

OUTLINE DIMENSIONS

Dimensions shown in inches and (mm).

14-Lead TSSOP Package (RU-14)



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